

ANTREX Electronics

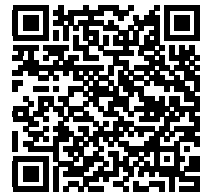
Electronic Components Sourcing Information

Product Reference Information

Part Number:	VS-16TTS16S-M3
Manufacturer:	Vishay General Semiconductor - Diodes Division
Package:	TO-263AB (D2PAK)
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/vishay-general-semiconductor-diodes-division-vs-16tts16s-m3.html>



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New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

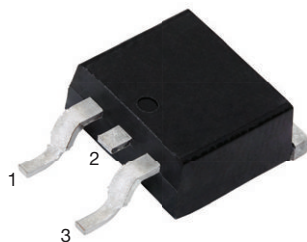
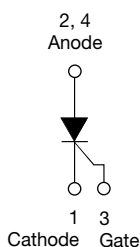
Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Thyristor Surface Mount Phase Control SCR, 16 A


D²PAK (TO-263AB)


FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

DESCRIPTION

The VS-16TTS16S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRIMARY CHARACTERISTICS

$I_{T(AV)}$	10 A
V_{DRM}/V_{RRM}	1600 V
V_{TM}	1.4 V
I_{GT}	60 mA
T_J	-40 °C to +125 °C
Package	D ² PAK (TO-263AB)
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	6.3	9.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	14.0	18.5	

Note

- $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
I_{RMS}		16	
V_{RRM}/V_{DRM}		1600	V
I_{TSM}		200	A
V_T	10 A, $T_J = 25$ °C	1.4	V
dV/dt		500	V/µs
dI/dt		150	A/µs
T_J		-40 to +125	°C

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-16TTS16S-M3	1600	1600	10

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
				TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 93\text{ }^{\circ}\text{C}$, 180° conduction, half sine wave		10		A
Maximum RMS on-state current	I_{RMS}			16		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied		170		
		10 ms sine pulse, no voltage reapplied		200		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied		144		A^2s
		10 ms sine pulse, no voltage reapplied		200		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied		2000		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	10 A, $T_J = 25\text{ }^{\circ}\text{C}$		1.4		V
On-state slope resistance	r_t	$T_J = 125\text{ }^{\circ}\text{C}$		24.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$			1.1		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^{\circ}\text{C}$	$V_R = \text{rated } V_{RRM}/V_{DRM}$		0.5	mA
		$T_J = 125\text{ }^{\circ}\text{C}$			10	
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$, $T_J = 25\text{ }^{\circ}\text{C}$		100	150	
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$		200		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J\text{ max. linear to }80\% V_{DRM} = R_g - k = \text{open}$		500		V/ μs
Maximum rate of rise of turned-on current	dI/dt			150		A/ μs

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^{\circ}\text{C}$	90	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	60	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	35	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^{\circ}\text{C}$	3.0	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^{\circ}\text{C}$, $V_{DRM} = \text{rated value}$	0.25	mA
Maximum DC gate current not to trigger	I_{GD}		2.0	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^{\circ}\text{C}$	0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^{\circ}\text{C}$	4	
Typical turn-off time	t_q		110	

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.3	°C/W
Typical thermal resistance, junction to ambient	R_{thJA}	PCB mount ⁽¹⁾	40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D ² PAK (TO-263AB)	16TTS16S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W.
For recommended footprint and soldering techniques refer to application note #AN-994

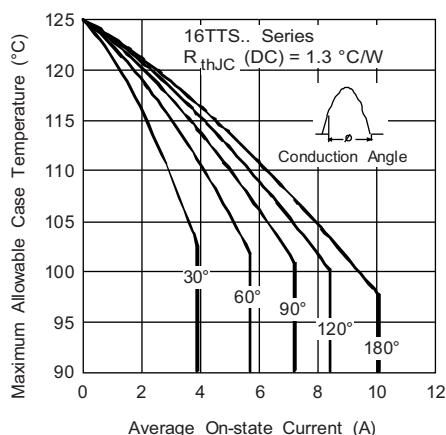


Fig. 1 - Current Rating Characteristics

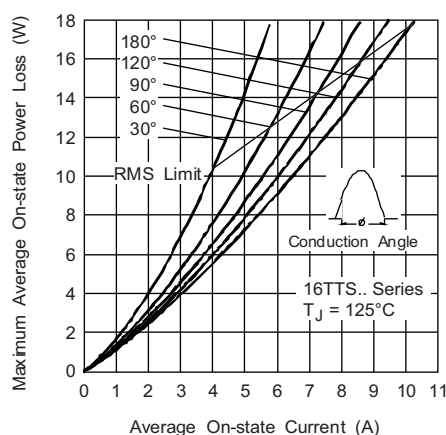


Fig. 3 - On-State Power Loss Characteristics

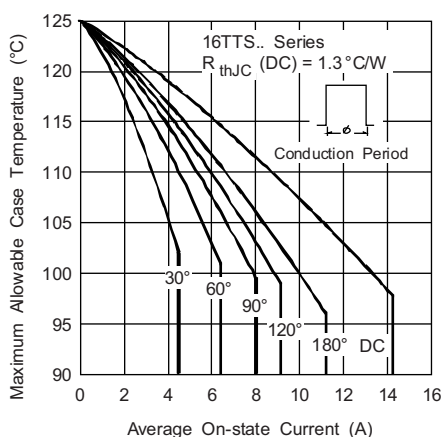


Fig. 2 - Current Rating Characteristics

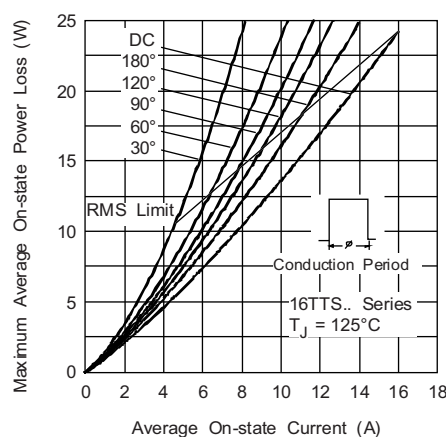


Fig. 4 - On-State Power Loss Characteristics

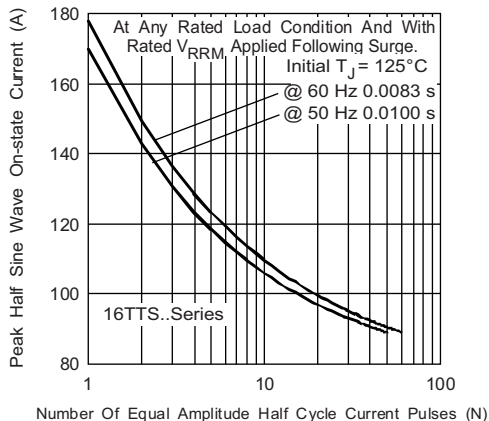


Fig. 5 - Maximum Non-Repetitive Surge Current

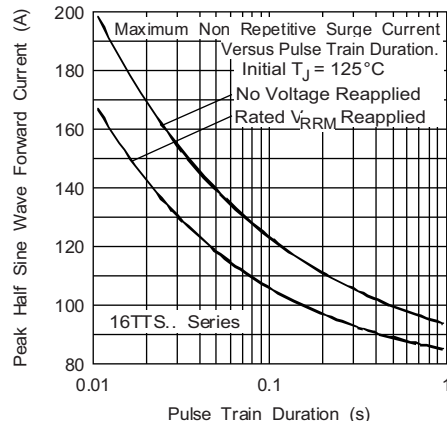


Fig. 6 - Maximum Non-Repetitive Surge Current

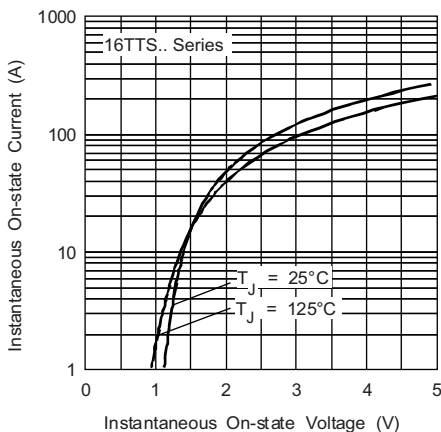
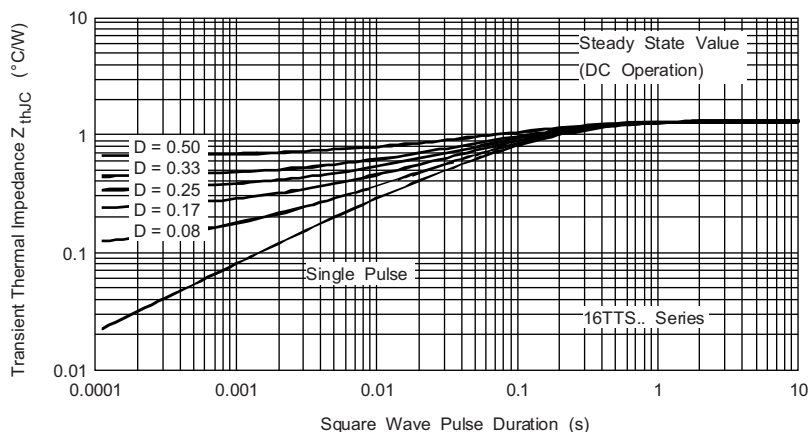


Fig. 7 - On-State Voltage Drop Characteristics


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

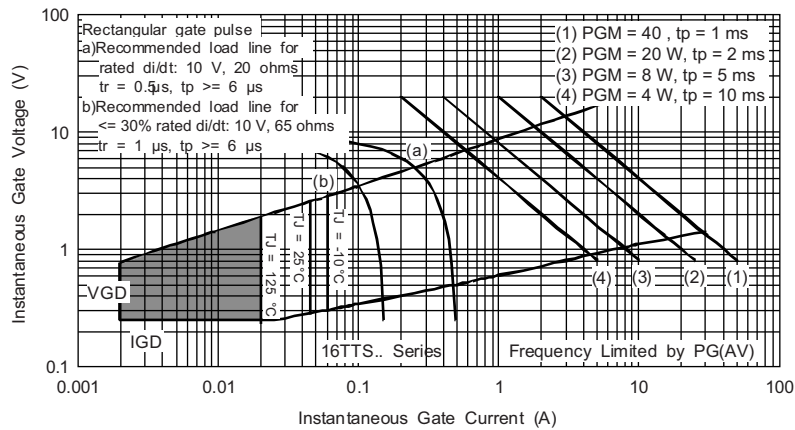


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	16	T	T	S	16	S	TRL	-M3
	1	2	3	4	5	6	7	8	9

- 1** - Vishay Semiconductors product
- 2** - Current rating
- 3** - Circuit configuration:
T = single thyristor
- 4** - Package:
T = D²PAK (TO-263AB)
- 5** - Type of silicon:
S = standard recovery rectifier
- 6** - Voltage rating: Voltage code x 100 = V_{RRM} (16 = 1600 V)
- 7** - S = surface mountable
- 8** -
 - None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9** - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)

PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-16TTS16S-M3	50	Antistatic plastic tubes
VS-16TTS16STRL-M3	800	13" diameter plastic tape and reel
VS-16TTS16STRR-M3	800	13" diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS

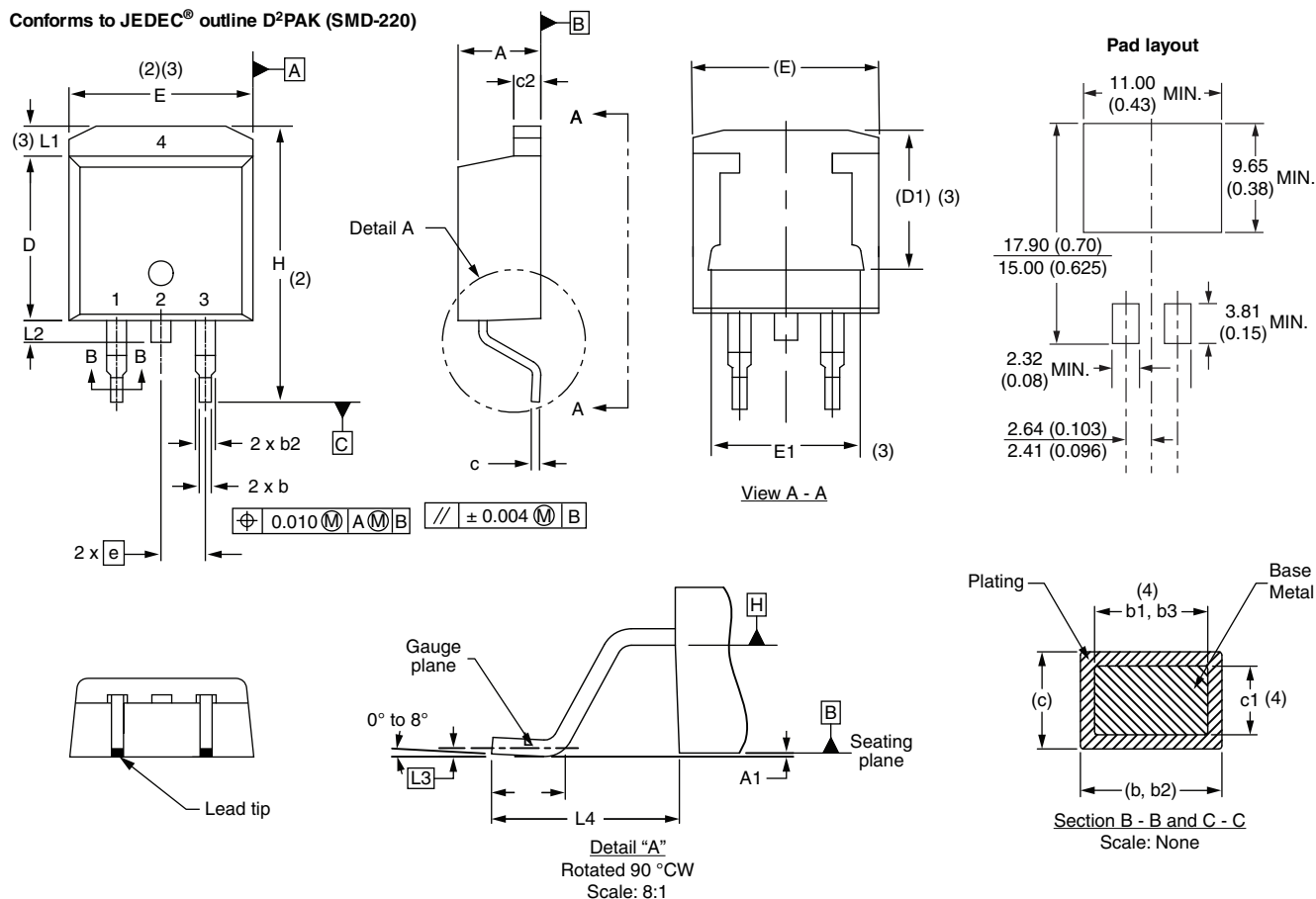
Dimensions	www.vishay.com/doc?96164
Part marking information	www.vishay.com/doc?95444
Packaging information	www.vishay.com/doc?96424



D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC® outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
c	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100 BSC		
H	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB



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